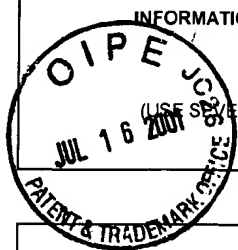


FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE
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SEPP12.001AUSAPPLICATION NO.
09/835,931INFORMATION DISCLOSURE STATEMENT
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Lindfors et al.FILING DATE
April 16, 2001GROUP
1765

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
[Signature]	1	5,855,680	1/5/99	Soininen et al.			
	2	4,389,973	6/28/93	Suntola et al.			
	3	4,058,430	11/15/77	Suntola et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

EXAMINER INITIAL		
[Signature]	4	Handbook of Crystal Growth 3, Thin Films and epitaxy, Part B. Growth Mechanisms and Dynamics, Page 625.
	5	Niinisto et al., "ALD precursor chemistry: evolution and future challenges," Journal de Physique IV. Vol. 9 (1999), pages Pr8-837-Pr8-852.
	6	M. Leskela et al., "Synthesis of oxide thin films and overlayers by atomic layer epitaxy for advanced applications," Materials Science & Engineering, Vol. B41 (1996), pages 23-29.
	7	Tuomo Suntola, "Atomic layer epitaxy," Thin Solid Films, Vol 216 (1992), pages 84-89

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EXAMINER	[Signature]	DATE CONSIDERED	9/9/02
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